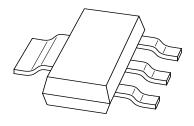
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## **BSP19**; **BSP20** NPN high-voltage transistors

Product data sheet Supersedes data of 1997 Mar 03 1999 Jun 01



## **NPN** high-voltage transistors

**BSP19**; **BSP20** 

#### **FEATURES**

• Low current (max. 100 mA)

• High voltage (max. 350 V).

#### **APPLICATIONS**

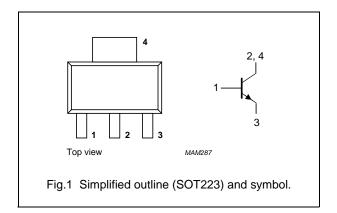
- Switching and amplification
- Especially used in telephony and automotive applications.

#### **DESCRIPTION**

NPN transistor in a SOT223 plastic package. PNP complement: BSP16.

#### **PINNING**

PIN	DESCRIPTION	
1	base	
2, 4	collector	
3	emitter	



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSP19		_	400	V
	BSP20		_	300	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSP19		_	350	V
	BSP20		_	250	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	100	mA
I <sub>B</sub>	base current (DC)		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1.2	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

 Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.
 For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

## NPN high-voltage transistors

BSP19; BSP20

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	104	K/W	
R <sub>th j-s</sub>	thermal resistance from junction to soldering point		23	K/W	

#### Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

#### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CE</sub> = 300 V	-	20	nA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 20 mA	40	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 4 \text{ mA}$	-	0.5	٧
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz}$	70	_	MHz

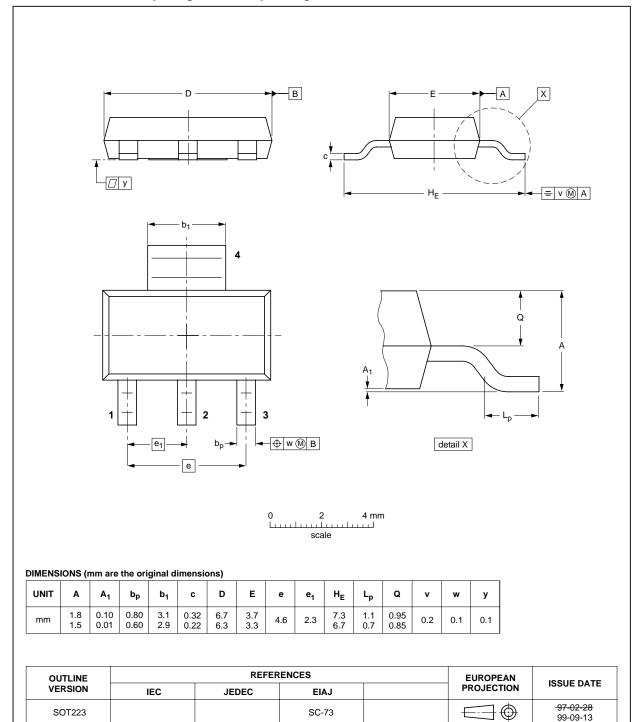
## NPN high-voltage transistors

BSP19; BSP20

#### **PACKAGE OUTLINE**

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

**SOT223** 



### **NPN** high-voltage transistors

**BSP19**; **BSP20** 

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

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#### **Contact information**

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